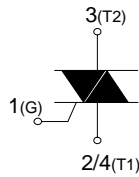
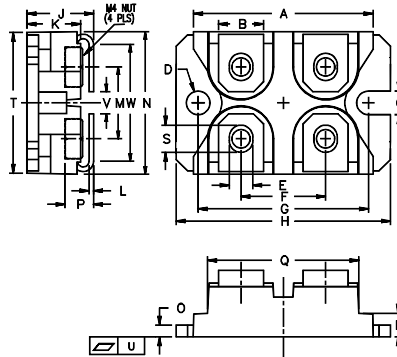


SBTA71G04S thru SBTA71G12S

Single Triac Module (Isolated)



Dimensions SOT-227(ISOTOP)



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.20	1.489	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004
V	3.30	4.57	0.130	0.180
W	0.760	0.830	0.030	0.033

	V_{DRM} V	V_{DSM} V
SBTA71G04S	400	450
SBTA71G06S	600	650
SBTA71G10S	1000	1100
SBTA71G12S	1200	1300

Symbol	Test Conditions	Maximum Ratings	Unit
I_{TRMS}	$T_{VJ}=58^{\circ}C$	70	A
I_{TSM}	$T_{VJ}=45^{\circ}C$ $V_R=0$ $t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	1080 1200	A
	$T_{VJ}=T_{VJM}$ $V_R=0$ $t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	750 800	
i^2t	$T_{VJ}=45^{\circ}C$ $V_R=0$ $t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	6000 5500	A^2s
	$T_{VJ}=T_{VJM}$ $V_R=0$ $t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	4350 4000	
$(di/dt)_{cr}$	$T_{VJ}=T_{VJM}$ $f=50Hz$, $t_p=200\mu s$ $V_D=2/3V_{DRM}$ $I_G=0.3A$ $di_G/dt=0.3A/\mu s$	repetitive, $I_T=40A$ 50	A/ μs
		non repetitive, $I_T=I_{TAVM}$ 300	
$(dv/dt)_{cr}$	$T_{VJ}=T_{VJM}$; $R_{GK}=\infty$; method 1 (linear voltage rise)	$V_{DR}=2/3V_{DRM}$ 500	V/ μs
P_{GM}	$T_{VJ}=T_{VJM}$ $I_T=I_{TAVM}$	$t_p=30\mu s$ 10 $t_p=300\mu s$ 5	W
P_{GAV}		1	W
V_{RGM}		10	V
T_{VJ} T_{VJM} T_{stg}		-40...+125 125 -40...+125	$^{\circ}C$
V_{ISOL}	50/60Hz, RMS $t=1$ minute, leads-to-tab	2500	V~
M_d	Mounting torque (M4)	1.1...1.5	Nm
Weight		30	g



SBTA71G04S thru SBTA71G12S

Single Triac Module (Isolated)

Symbol	Test Conditions	Characteristic Values	Unit
I_R, I_D	$T_{VJ}=T_{VJM}; V_D=V_{DRM}$	10	mA
V_{TM}	$I_T=100A; T_{VJ}=25^{\circ}C$	1.55	V
V_{TO}	For power-loss calculations only ($T_{VJ}=125^{\circ}C$)	0.85	V
r_T		11	mΩ
V_{GT}	I II III IV $V_D=6V; I_T=1A; T_{VJ}=25^{\circ}C$	1.3	V
		1.3	
		1.3	
		1.5	
I_{GT}	I II III IV $V_D=6V; I_T=1A; T_{VJ}=25^{\circ}C$	50	mA
		50	
		50	
		100	
V_{GD}	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	0.2	V
I_{GD}		10	mA
I_H	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	100	mA
R_{thJC}	DC current	0.2	K/W
R_{thJH}	DC current	0.1	K/W
a	Max. acceleration, 50 Hz	50	m/s ²

Sirectifier[®]

SBTA71G04S thru SBTA71G12S

Single Triac Module (Isolated)

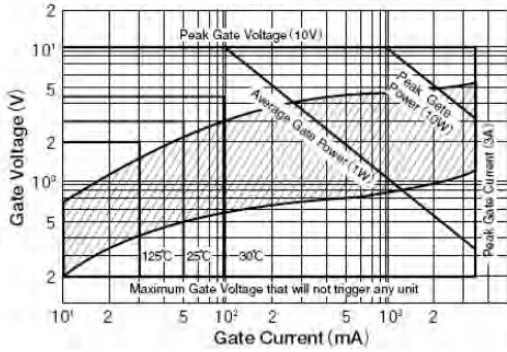


Fig. 1 Gate Characteristics

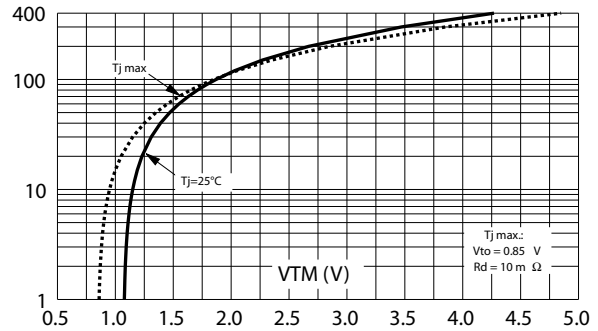


Fig. 2 On-state characteristics

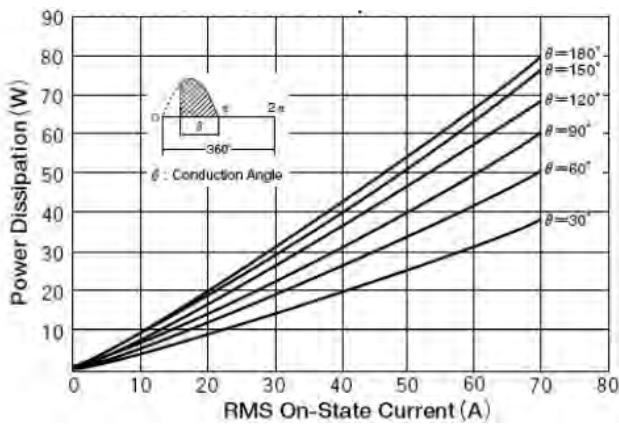


Fig. 3 On-state Current vs. Maximum Power Dissipation

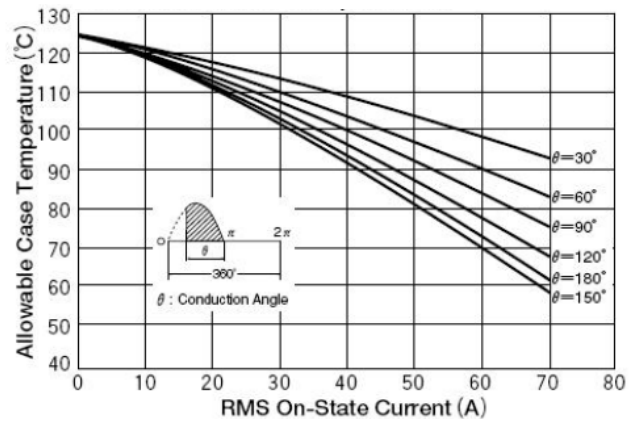


Fig. 4 On-state Current vs. Allowable Case Temperature

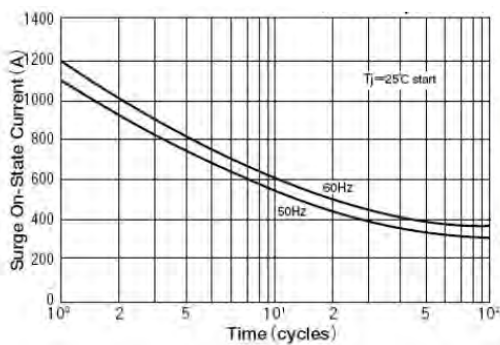


Fig. 5 Surge On-state Current Rating(Non-Repetitive)

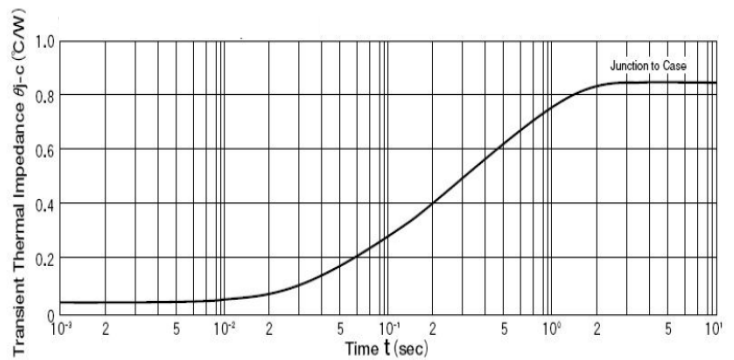


Fig. 6 Transient Thermal Impedance

